

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 108272.02		APPLICATION NO. Rule 53(b) Continuing Application of U.S. Application No. 09/748,207	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Yoshitaka SASAKI et al.		10/790,049	
				FILING DATE March 2, 2004			

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
ADT	1	6,083,410	07/2000	Ikegawa et al.	-	
	2	6,333,841	12/2001	Sasaki	-	
ADT	3	6,459,551	10/2002	Hayakawa	-	

FOREIGN PATENT DOCUMENTS						
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS		
ADT	4	JP A 4-232250	08/1992	Japan		
	5	JP A 9-91618	04/1997	Japan		
	6	JP A 11-353616	12/1999	Japan		
	7	JP A 11-39614	12/1999	Japan		
ADT	8	WO 99/41739	08/1999	WIPO		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)	
ADT	Ericsson et al.; "Properties of Al ₂ O ₃ -films deposited on silicon by atomic layer epitaxy"; Microelectronic Engineering 36 (1997) 91-94

EXAMINER	/A. Dexter Tugbang/	DATE CONSIDERED	1/18/07
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Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: March 2, 2004